

## Contents

|   |    |
|---|----|
| Preface . . . . .   | ix |
| Organizers and Sponsors . . . . .   | x  |
| <b>Silicon, SOI</b>   |    |
| Silicon-on-insulator technology for high-temperature, smart-power applications . . . . .<br>J. Korec (Frankfurt, Germany)   | 1  |
| Silicon-on-insulator technology for high temperature metal oxide semiconductor devices and circuits . . . . .<br>D. Flandre (Louvain-la-Neuve, Belgium)   | 7  |
| Static and dynamic behaviour of power devices in silicon-direct-bonded substrates . . . . .<br>U. Apel, H.-G. Graf, C. Harendt and B. Höfflinger (Stuttgart, Germany)   | 13 |
| Tungsten metallization technology for high temperature silicon-on-insulator devices . . . . .<br>J. Chen and J.-P. Colinge (Louvain-la-Neuve, Belgium)  | 18 |
| Analysis of SIMOX metal-oxide-semiconductor transistors operated in the high temperature range . . . . .<br>T. Ouisse, G. Reichert, S. Cristoloveanu, O. Faynot and B. Giffard (Grenoble, France)   | 21 |
| A study of the growth and shrinkage of stacking faults in SIMOX . . . . .<br>G. Silvestre, R.A. Moore (Dublin, Ireland), A. Garcia and B. Aspar (Grenoble, France)  | 24 |
| Strain reduction in the Si overlayer for improved SIMOX material . . . . .<br>S.L. Ellingboe and M.C. Ridgway (Canberra, Australia)   | 29 |
| Monte Carlo simulation of growth and recovery of silicon. . . . .<br>S. Keršulis and V. Mitin (Detroit, MI, USA)  | 34 |
| Temperature dependence of the thin film silicon-on-insulator field effect transistor current characteristics based on full solution for the one-dimensional MISIS structure . . . . .<br>S. Scheinert (Ilmenau, Germany) and G. Paasch (Dresden, Germany) | 38 |
| Comparison of properties of solid phase epitaxial silicon on sapphire films recrystallized by rapid thermal annealing and furnace annealing . . . . .<br>Q. Wang, Y. Zan, J. Wang and Y. Yu (Beijing, People's Republic of China)                         | 43 |
| <b>III-V Compounds</b>  |    |
| III-V Semiconductor properties for high-temperature electronics. . . . .<br>H.L. Hartnagel (Darmstadt, Germany)   | 47 |
| A complementary III-V heterostructure field effect transistor technology for high temperature integrated circuits . . . . .<br>C. Wilson, A. O'Neill (Newcastle upon Tyne, UK), S. Baier and J. Nohava (Bloomington, MN, USA)                             | 54 |
| Metal-organic chemical vapor deposition growth of GaN. . . . .<br>D.-c. Lu, D. Wang, X. Wang, X. Liu, J. Dong, W. Gao, C. Li and Y. Li (Beijing, People's Republic of China)  | 58 |
| Determination of the GaN/AlN band discontinuities via the ( $-/0$ ) acceptor level of iron . . . . .<br>J. Baur, M. Kunzer, K. Maier, U. Kaufmann and J. Schneider (Freiburg, Germany)  | 61 |
| The optical properties and electronic transitions of cubic and hexagonal GaN films between 1.5 and 10 eV. . . . .<br>S. Logothetidis, J. Petalas (Thessaloniki, Greece), M. Cardona (Stuttgart, Germany) and T.D. Moustakas (Boston, MA, USA)             | 65 |
| Investigations on Pd/In-based high temperature stable ohmic contacts on GaAs by X-ray reflectometry and diffractometry . . . . .<br>T. Pirling, K. Fricke, M. Schüßler, W.Y. Lee, H. Fueß and H.L. Hartnagel (Darmstadt, Germany)                         | 70 |
| How to induce the epitaxial growth of gallium nitride on Si(001) . . . . .<br>U. Rössner, A. Barski, J.L. Rouvière, A. Bourret (Grenoble, France), J. Massies, C. Deparis and N. Grandjean (Valbonne, France)   | 74 |

|   |     |
|---|-----|
| Development of chemical beam epitaxy for the deposition of gallium nitride . . . . .  | 78  |
| C.R. Kingsley, T.J. Whitaker (Oxford, UK), A.T.S. Wee (Singapore, Singapore), R.B. Jackman (London, UK) and J.S. Foord (Oxford, UK)   |     |
| <b>SiC</b>  |     |
| Growth of bulk SiC . . . . .  | 83  |
| Yu.M. Tairov (St. Petersburg, Russia)   |     |
| Study of SiC single-crystal sublimation growth conditions. . . . .  | 90  |
| I. Garçon (Grenoble, France), A. Rouault (St. Martin d'Hères, France), M. Anikin, C. Jaussaud (Grenoble, France) and R. Madar (St. Martin d'Hères, France)  |     |
| Sputtering effects in hexagonal silicon carbide . . . . .   | 94  |
| J. Pezoldt, B. Stottko, G. Kupris and G. Ecke (Ilmenau, Germany)  |     |
| Are polytype transitions possible during boron diffusion? . . . . .   | 99  |
| J. Pezoldt (Ilmenau, Germany)   |     |
| Formation of $\beta$ -SiC films by ion beam mixing of Si/C multilayers . . . . .  | 105 |
| J.P. Rivière, M. Zaytouni, M.F. Denanot and J. Allain (Poitiers, France)  |     |
| Observation of Si out-diffusion related defects in SiC growth on Si(001) . . . . .  | 110 |
| M. Diani (Mulhouse, France), A. Mesli (Strasbourg, France), L. Kubler (Mulhouse, France), A. Claverie (Toulouse, France), J.L. Balladore (Strasbourg, France), D. Aubel (Mulhouse, France), S. Peyre, T. Heiser (Strasbourg, France) and J.L. Bischoff (Mulhouse, France) |     |
| Fabrication and properties of high-resistivity porous silicon carbide for SiC power device passivation . . . . .  | 114 |
| A.O. Konstantinov, C.I. Harris, A. Henry and E. Janzén (Linköping, Sweden)  |     |
| Magnetic circular dichroism and electron spin resonance of the $A^-$ acceptor state of vanadium, $V^{3+}$ , in 6H-SiC . . . . .   | 118 |
| M. Kunzer, U. Kaufmann, K. Maier and J. Schneider (Freiburg, Germany)   |     |
| Determination of donor and acceptor level energies by admittance spectroscopy in 6H SiC . . . . .   | 122 |
| C. Raynaud, C. Richier, P.N. Brounkov, F. Ducroquet, G. Guillot (Villeurbanne, France), L.M. Porter, R.F. Davis (Raleigh, NC, USA), C. Jaussaud and T. Billon (Grenoble, France)  |     |
| Interfacial reactions of W thin film on single-crystal (001) $\beta$ -SiC . . . . .   | 126 |
| L. Baud, C. Jaussaud (Grenoble, France), R. Madar, C. Bernard (Saint Martin d'Hères, France), J.S. Chen and M.A. Nicolet (Pasadena, CA, USA)  |     |
| Effects of Ar and $H_2$ annealing on the electrical properties of oxides on 6H SiC . . . . .  | 131 |
| E. Stein von Kamiński, A. Götz and H. Kurz (Aachen, Germany)  |     |
| Unintentional incorporation of contaminants during chemical vapour deposition of silicon carbide . . . . .  | 134 |
| S. Karmann, L. Di Cioccio, B. Blanchard, T. Ouisse, D. Muyard and C. Jaussaud (Grenoble, France)  |     |
| Carbonization of Si surfaces by solid source molecular beam epitaxy . . . . .   | 138 |
| K. Zekentes, R. Callec, K. Tsagaraki, B. Sagnes (Heraklion, Greece), G. Arnaud, J. Pascual (Bellaterra, Spain) and J. Camassel (Montpellier, France)  |     |
| Defect production and annealing in ion implanted silicon carbide. . . . .   | 142 |
| A. Heft, E. Wendler, T. Bachmann, E. Glaser and W. Wesch (Jena, Germany)  |     |
| Electronic transport in thermally crystallized SiC films on sapphire. . . . .   | 147 |
| W. Hellmich, G. Müller, G. Krötz (Munich, Germany), G. Derst and S. Kalbitzer (Heidelberg, Germany)   |     |
| Deposition and optical properties of amorphous hydrogenated $Si_xC_y$ layers . . . . .  | 151 |
| A.A. Chumakov, P.V. Bulkin, P.L. Swart, B.M. Lacquet and A.A. Scherbakov (Auckland Park, South Africa)  |     |
| Structural and electronic characterization of $\beta$ -SiC films on Si grown from mono-methylsilane precursors . . . . .  | 154 |
| G. Krötz, W. Legner, G. Müller (Munich, Germany), H.W. Grueninger (Frankfurt, Germany), L. Smith, B. Leese, A. Jones and S. Rushworth (Merseyside, UK)  |     |
| Structural, optical and electrical properties of state of the art cubic SiC films . . . . .   | 160 |
| J. Stoemenos (Thessaloniki, Greece), C. Dezaudier (Montpellier, France), G. Arnaud (Bellaterra, Spain), S. Contreras, J. Camassel (Montpellier, France), J. Pascual (Bellaterra, Spain) and J.L. Robert (Montpellier, France)   |     |
| X-ray photoelectron spectroscopy study of $Sn^+$ implanted $a-Si_{1-x}C_x:H$ thin films . . . . .   | 165 |
| N. Tzenov, D. Dimova-Malinovska, Ts. Marinova, V. Krastev and T. Tsvetkova (Sofia, Bulgaria)  |     |
| Growth of thin $\beta$ -SiC layers by carbonization of Si surfaces by rapid thermal processing . . . . .  | 170 |
| V. Cimalla, K.V. Karagodina, J. Pezoldt and G. Eichhorn (Ilmenau, Germany)  |     |

|   |     |
|---|-----|
| Reactive ion etching characterization of a-SiC:H in CF <sub>4</sub> /O <sub>2</sub> plasma . . . . .  | 176 |
| G. Saggio, E. Verona, P. Di Rosa, S. La Monica, R. Salotti and L. Schirone (Rome, Italy)  |     |
| Deep centers and electroluminescence in 4H-SiC diodes with p-type base region. . . . .  | 181 |
| N.I. Keznetsov and A.S. Zubrilov (St. Petersburg, Russia)   |     |
| Contact resistivity of Re, Pt and Ta films on n-type $\beta$ -SiC: preliminary results. . . . .   | 185 |
| J.S. Chen, A. Bächli, M.-A. Nicolet (Pasadena, CA, USA), L. Baud, C. Jaussaud (Grenoble, France) and R. Madar (Saint Martin d'Hères, France)                                |     |
| High temperature silicon carbide stabilitrans for the voltage range from 4 to 50 V . . . . .  | 190 |
| A.N. Andreev, M.M. Anikin, V.V. Zelenin, P.A. Ivanov, A.A. Lebedev, M.G. Rastegaeva, N.S. Savkina, A.M. Strel'chuk, A.L. Syrkin and V.E. Chelnokov (St. Petersburg, Russia) |     |
| High temperature 6H-SiC dinistor . . . . .  | 194 |
| A.N. Andreev, A.M. Strel'chuk, N.S. Savkina, F.M. Snegov and V.E. Chelnokov (St. Petersburg, Russia)  |     |
| Surface barrier height in metal-n-6H-SiC structures . . . . .   | 198 |
| A.L. Syrkin (Grenoble, France), A.N. Andreev, A.A. Lebedev, M.G. Rastegaeva and V.E. Chelnokov (St. Petersburg, Russia)   |     |
| <b>Diamond</b>  |     |
| Macrodefect formation in semiconductors during high energy ion implantation: Monte Carlo simulation of damage depth distributions. . . . .                                  | 202 |
| S.A. Fedotov, V.S. Varichenko, A.M. Zaitsev (Hagen, Germany), M. Ishimaru, Y. Hiroyama and T. Motooka (Fukuoka, Japan)  |     |
| High temperature contacts to chemically vapour deposited diamond films—reliability issues . . . . .   | 206 |
| C. Johnston, P.R. Chalker, I.M. Buckley-Golder (Didcot, UK), M. van Rossum (Leuven, Belgium), M. Werner and E. Obermeier (Berlin, Germany)                                  |     |
| Boron doped diamond films: electrical and optical characterization and the effect of compensating nitrogen . . . . .  | 211 |
| R. Locher, J. Wagner, F. Fuchs, C. Wild, P. Hiesinger, P. Gonon and P. Koidl (Freiburg, Germany)  |     |
| Chemical vapour deposition of diamond from a novel capacitively coupled r.f. plasma source . . . . .  | 216 |
| R.B. Jackman, J. Beckman (London, UK) and J.S. Foord (Oxford, UK)   |     |
| Structure of nitrogen-substituted graphite prepared by chemical vapor deposition . . . . .  | 220 |
| T. Matsui, M. Yudasaka, R. Kikuchi, Y. Ohki and S. Yoshimura (Kawasaki, Japan)  |     |
| High temperature stability of chemically vapour deposited diamond diodes. . . . .   | 223 |
| R.D. McKeag, S.S.M. Chan (London, UK), C. Johnston, P.R. Chalker (Didcot, UK) and R.B. Jackman (London, UK)   |     |
| <b>Power conversion</b>   |     |
| Boron-rich solids: a chance for high-efficiency high-temperature thermoelectric energy conversion. . . . .  | 228 |
| H. Werheit (Duisburg, Germany)  |     |
| Diffusion controlled degradation analysis of high temperature (Bi,Sb) <sub>2</sub> (Te,Se) <sub>3</sub> semiconductor thermoelectric power modules . . . . .                | 233 |
| C. Huang and A. Christou (College Park, MD, USA)  |     |
| AUTHOR INDEX . . . . .  | 237 |
| SUBJECT INDEX . . . . .   | 239 |

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